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Publication date: 2015

Document Version Publisher's PDF, also known as Version of record

Link back to DTU Orbit

Citation (APA):

Thomsen, J. D., Gade, C., Bøggild, P., & Booth, T. (2015). In-situ TEM patterning and electrical characterisation of graphene. Poster session presented at 6th Symposium on Carbon and Related Nanomaterials, Copenhagen, Denmark.

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In-situ TEM patterning and electrical characterisation of graphene

Joachim D. Thomsen, Carsten Gade, Peter Bøggild, Timothy J. Booth DTU Nanotech, Technical University of Denmark, 2800 Kgs. Lyngby, Denmark

jdth@nanotech.dtu.dk

Introduction

- Transmission electron microscopy is an excellent characterisation tool for obtaining information about the graphene structure on an atomic scale
- It can be used to shape the graphene as well as other 2D materials (hBN, MoS₂, etc) through (1) knock-on damage from the beam^{1, 2}, (2) etching via oxygen or water (in an environmental TEM), (3) nanoparticle induced etching³.

Graphene Constrictions

1. Using knock-on damage we can structure the graphene by focusing the beam to a small area, in this case forming a constriction.



- We have fabricated silicon microchips that fit into a standard TEM holder, with electrodes to measure the electrical properties of graphene as well as for heating the samples.
- Here we present our preliminary work with graphene in-situ TEM, correlating structural changes and electrical properties



Experimental platform on TEM sample holder



- 1. "Correlating Atomic Structure and Transport in Suspended Graphene Nanoribbons", Z. J. Qi et al, Nano Lett. 11 (2014), 5184-5188
- 2. "Atomic-Scale Electron-Beam Sculpting of Near-Defect-Free Graphene Nanostructures", B. Song et al, Nano Lett. 11 (2011), 2247-2250
- 3. Discrete Dynamics of Nanoparticle Channelling in Suspended Graphene. T. J. Booth et al, Nano Lett. 11 (2011), 2689-2692
- **ॻ** 8,0x10⁻⁵ [ime (min) 2. After sculpting, the voltage 3. High resolution images of the across the constriction was broken area shows some increased until breakage indications of heating Current over the constriction and its derivative vs. time 5.0x10⁻ 4,0x10⁻⁴ Current (A) 3.0x10⁻⁴ 2,0x10⁻⁴ 1,0x10⁻⁴ 0.0 5⁄x10⁻⁵ 4x10⁻⁵ dl/dt (A/s) 3x10⁻⁵ 2x10⁻⁵ 1x10⁻⁵ 130 140 150 160 170 180 190 200 210 Time (s)

TEM Platforms

Twisted Bilayers

TEM chips: Silicon nitride membrane with embedded Pt heaters and surface electrode structures for electrical measurements.

Schematic of the 4 terminal contact chip.



Chip glowing 4-point heater hot in normal structure atmosphere

137

0 V,

Twisted bilayers - stacked incommensurate monolayers – were made using wedging transfer. The stack is then transferred to the TEM platform.



10 twisted bilayer devices were characterised. While most samples showed linear IV characteristics, this sample showed a diode-like behavior

Four-terminal measurement



Bilaye

S

ingle

layer











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